February 1988

CD40106BM/CD40106BC Hex Schmitt Trigger

General Description

The CD40106B Hex Schmitt Trigger is a monolithic complementary MOS (CMOS) integrated circuit constructed with N and P-channel enhancement transistors. The positive and negative-going threshold voltages, V_{T+} and V_{T-} , show low variation with respect to temperature (typ 0.0005V/°C at $V_{DD}=$ 10V), and hysteresis, $V_{T+}-V_{T-}\geq 0.2\ V_{DD}$ is guaranteed.

All inputs are protected from damage due to static discharge by diode clamps to V_{DD} and V_{SS} .

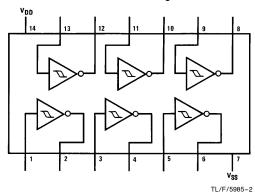
Features

- Wide supply voltage range
- 3V to 15V 0.7 V_{DD} (typ.)
- High noise immunity
- Fan out of 2 driving 74L
- Low power TTL compatibility
- or 1 driving 74LS 0.4 V_{DD} (typ.)

- Hysteresis
- 0.2 V_{DD} guaranteed
- Equivalent to MM54C14/MM74C14
- Equivalent to MC14584B

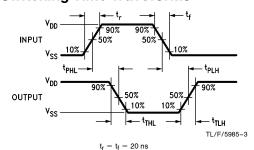
Connection Diagram

Dual-In-Line Package



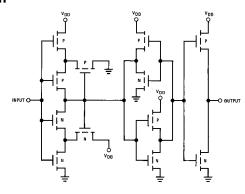
Top View

Switching Time Waveforms



Order Number CD40106B

Schematic Diagram



TL/F/5985-1

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{ll} \text{DC Supply Voltage (V}_{\text{DD}}) & -0.5 \text{ to } +18 \text{ V}_{\text{DC}} \\ \text{Input Voltage (V}_{\text{IN}}) & -0.5 \text{ to V}_{\text{DD}} +0.5 \text{ V}_{\text{DC}} \\ \text{Storage Temperature Range (T}_{\text{S}}) & -65^{\circ}\text{C to } +150^{\circ}\text{C} \end{array}$

Power Dissipation (PD)

 Dual-In-Line
 700 mW

 Small Outline
 500 mW

Lead Temperature (T_L) (Soldering, 10 seconds)

260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD}) $$3$ to 15$ V_{DC}$ lnput Voltage (V_{IN}) 0 to V_{DD} V_{DC}$ }$

Operating Temperature Range (T_A) CD40106BM

DC Electrical Characteristics CD40106BM (Note 2)

Symbol	Parameter	Conditions	−55°C		+ 25°C			+ 125°C		Units
Symbol			Min	Max	Min	Тур	Max	Min	Max	511113
I _{DD}	Quiescent Device Current	$V_{DD} = 5V$, $V_{IN} = V_{DD}$ or V_{SS}		1.0			1.0		30	μΑ
		$V_{DD} = 10V,$ $V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{DD} = 15V,$		2.0 4.0			2.0 4.0		60 120	μA μA
		$V_{IN} = V_{DD}$ or V_{SS}								
V _{OL}	Low Level Output Voltage	$\begin{aligned} I_O &< 1 \; \mu A \\ V_{DD} &= 5 V \\ V_{DD} &= 10 V \\ V_{DD} &= 15 V \end{aligned}$		0.05 0.05 0.05			0.05 0.05 0.05		0.05 0.05 0.05	V V V
V _{OH}	High Level Output Voltage	$\begin{aligned} I_O &< 1 \; \mu A \\ V_{DD} &= 5 V \\ V_{DD} &= 10 V \\ V_{DD} &= 15 V \end{aligned}$	4.95 9.95 14.95		4.95 9.95 14.95	5 10 15		4.95 0.95 14.95		V V V
V _T -	Negative-Going Threshold Voltage	$V_{DD} = 5V, V_{O} = 4.5V$ $V_{DD} = 10V, V_{O} = 9V$ $V_{DD} = 15V, V_{O} = 13.5V$	0.7 1.4 2.1	2.0 4.0 6.0	0.7 1.4 2.1	1.4 3.2 5.0	2.0 4.0 6.0	0.7 1.4 2.1	2.0 4.0 6.0	V V
V _T +	Positive-Going Threshold Voltage	$V_{DD} = 5V, V_{O} = 0.5V$ $V_{DD} = 10V, V_{O} = 1V$ $V_{DD} = 15V, V_{O} = 1.5V$	3.0 6.0 9.0	4.3 8.6 12.9	3.0 6.0 9.0	3.6 6.8 10.0	4.3 8.6 12.9	3.0 6.0 9.0	4.3 8.6 12.9	V V V
V _H	Hysteresis (V _{T+} - V _{T-})	$V_{DD} = 5V$ $V_{DD} = 10V$ $V_{DD} = 15V$	1.0 2.0 3.0	3.6 7.2 10.8	1.0 2.0 3.0	2.2 3.6 5.0	3.6 7.2 10.8	1.0 2.0 3.0	3.6 7.2 10.8	V V V
l _{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V, V_{O} = 0.4V$ $V_{DD} = 10V, V_{O} = 0.5V$ $V_{DD} = 15V, V_{O} = 1.5V$	0.64 1.6 4.2		0.51 1.3 3.4	0.88 2.25 8.8		0.36 0.9 2.4		mA mA mA
ГОН	High Level Output Current (Note 3)	$V_{DD} = 5V, V_{O} = 4.6V$ $V_{DD} = 10V, V_{O} = 9.5V$ $V_{DD} = 15V, V_{O} = 13.5V$	-0.64 -1.6 -4.2		-0.51 -1.3 -3.4	-0.88 -2.25 -8.8		-0.36 -0.9 -2.4		mA mA mA
I _{IN}	Input Current	V _{DD} =15V, V _{IN} =0V V _{DD} =15V, V _{IN} =15V		-0.10 0.10		-10 ⁻⁵	-0.10 0.10		-1.0 1.0	μA μA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

DC Electrical Characteristics CD40106BC (Note 2)

Symbol	Parameter	Conditions	-40°C		+ 25°C			+85°C		Units
			Min	Max	Min	Тур	Max	Min	Max	Jillis
I _{DD}	Quiescent Device Current	$V_{DD} = 5V$ $V_{DD} = 10V$ $V_{DD} = 15V$		4.0 8.0 16.0			4.0 8.0 16.0		30 60 120	μΑ μΑ μΑ
V _{OL}	Low Level Output Voltage	$ I_{O} < 1 \mu A$ $V_{DD} = 5V$ $V_{DD} = 10V$ $V_{DD} = 15V$		0.05 0.05 0.05			0.05 0.05 0.05		0.05 0.05 0.05	V V V
V _{OH}	High Level Output Voltage	$\begin{aligned} & I_O < 1 \; \mu A \\ &V_{DD} = 5V \\ &V_{DD} = 10V \\ &V_{DD} = 15V \end{aligned}$	4.95 9.95 14.95		4.95 9.95 14.95	5 10 15		4.95 0.95 14.95		V V V
V _T -	Negative-Going Threshold Voltage	$V_{DD} = 5V, V_{O} = 4.5V$ $V_{DD} = 10V, V_{O} = 9V$ $V_{DD} = 15V, V_{O} = 13.5V$	0.7 1.4 2.1	2.0 4.0 6.0	0.7 1.4 2.1	1.4 3.2 5.0	2.0 4.0 6.0	0.7 1.4 2.1	2.0 4.0 6.0	V V
V _{T+}	Positive-Going Threshold Voltage	$V_{DD} = 5V, V_{O} = 0.5V$ $V_{DD} = 10V, V_{O} = 1V$ $V_{DD} = 15V, V_{O} = 1.5V$	3.0 6.0 9.0	4.3 8.6 12.9	3.0 6.0 9.0	3.6 6.8 10.0	4.3 8.6 12.9	3.0 6.0 9.0	4.3 8.6 12.9	V V V
V _H	Hysteresis (V _{T+} - V _{T-}) Voltage	$V_{DD} = 5V$ $V_{DD} = 10V$ $V_{DD} = 15V$	1.0 2.0 3.0	3.6 7.2 10.8	1.0 2.0 3.0	2.2 3.6 5.0	3.6 7.2 10.8	1.0 2.0 3.0	3.6 7.2 10.8	V V V
l _{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V, V_{O} = 0.4V$ $V_{DD} = 10V, V_{O} = 0.5V$ $V_{DD} = 15V, V_{O} = 1.5V$	0.52 1.3 3.6		0.44 1.1 3.0	0.88 2.25 8.8		0.36 0.9 2.4		mA mA mA
I _{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V, V_{O} = 4.6V$ $V_{DD} = 10V, V_{O} = 9.5V$ $V_{DD} = 15V, V_{O} = 13.5V$	-0.52 -1.3 -3.6		-0.44 -1.1 -3.0	-0.88 -2.25 -8.8		-0.36 -0.9 -2.4		mA mA mA
I _{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$ $V_{DD} = 15V, V_{IN} = 15V$		-0.30 0.30		-10 ⁻⁵	-0.30 0.30		-1.0 1.0	μΑ μΑ

AC Electrical Characteristics*

 $\rm T_A = 25^{\circ}\rm C,\, C_L = 50~pF,\, R_L = 200k,\, t_{\rm f}$ and $\rm t_{\rm f} = 20~ns,\, unless$ otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PHL} or t _{PLH}	Propagation Delay Time from	$V_{DD} = 5V$		220	400	ns
	Input to Output	$V_{DD} = 10V$		80	200	ns
		$V_{DD} = 15V$		70	160	ns
t _{THL} or t _{TLH}	Transition Time	$V_{DD} = 5V$		100	200	ns
		$V_{DD} = 10V$		50	100	ns
		$V_{DD} = 15V$		40	80	ns
C _{IN}	Average Input Capacitance	Any Input		5	7.5	pF
C _{PD}	Power Dissipation Capacity	Any Gate (Note 4)		14		pF

^{*}AC Parameters are guaranteed by DC correlated testing.

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

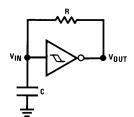
Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: $I_{\mbox{\scriptsize OH}}$ and $I_{\mbox{\scriptsize OL}}$ are tested one output at a time.

Note 4: C_{PD} determines the no load ac power consumption of any CMOS device. For complete explanation see 54C/74C Family Characteristics Application Note, AN-90.

Typical Applications

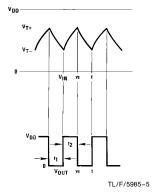
Low Power Oscillator



$$\begin{split} t_1 &\approx \text{RC } \ell \, n \, \frac{V_{T+}}{V_{T-}} \\ t_2 &\approx \text{RC } \ell \, n \, \frac{V_{DD} - V_{T-}}{V_{DD} - V_{T+}} \\ f &\approx \frac{1}{\text{RC } \ell \, n \, \frac{V_{T+} \left(V_{DD} - V_{T-}\right)}{V_{T-} \left(V_{DD} - V_{T+}\right)} \end{split}$$

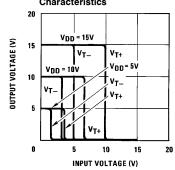
Note: The equations assume $t_1 \ + \ t_2 >> \ t_{PHL} \ + \ t_{PLH}$

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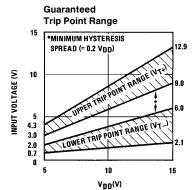


Typical Performance Characteristics

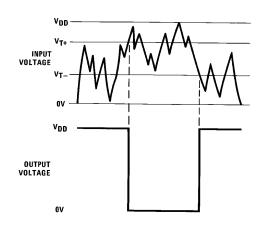
Typical Transfer Characteristics



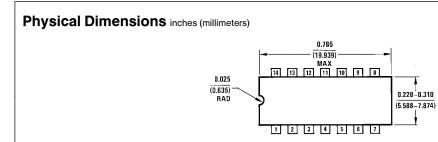
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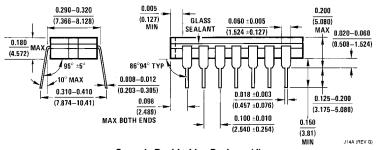


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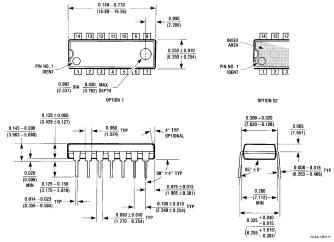
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Ceramic Dual-In-Line Package (J) Order Number CD40106BMJ or CD40106BCJ NS Package Number J14A

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number CD40106BMN or CD40106BCN NS Package Number N14A

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